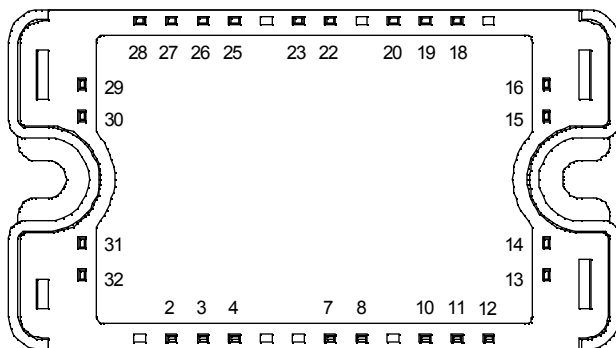
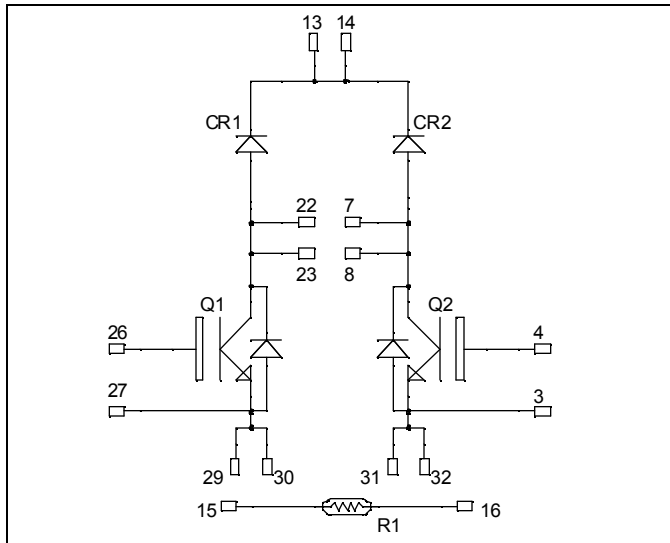


Dual Boost chopper PT IGBT Power Module

$$V_{CES} = 600V$$

$$I_C = 30A @ T_c = 80^{\circ}C$$



All multiple inputs and outputs must be shorted together
Example: 13/14 ; 29/30 ; 22/23 ...

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Power MOS 7® Punch Through (PT) IGBT
 - Low conduction loss
 - Ultra fast tail current shutoff
 - Low gate charge
 - Switching frequency capability in the 200kHz range
 - Soft recovery parallel diodes
 - Low diode VF
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a single boost of twice the current capability.

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	600	V
I_C	Continuous Collector Current	$T_c = 25^{\circ}C$ 48 $T_c = 80^{\circ}C$ 30	A
I_{CM}	Pulsed Collector Current	$T_c = 25^{\circ}C$ 120	A
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_c = 25^{\circ}C$ 156	W
SSOA	Switching Safe Operating Area	$T_j = 150^{\circ}C$ 120A @ 600V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
BV_{CES}	Collector - Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 500\mu A$	600			V
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V$ $V_{CE} = 600V$			500 3000	μA
$V_{CE(on)}$	Collector Emitter on Voltage	$V_{GE} = 15V$ $I_C = 30A$		2.2 2.1	2.7	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1mA$	3		6	V
I_{GES}	Gate - Emitter Leakage Current	$V_{GE} = \pm 20V, V_{CE} = 0V$			± 100	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V$		3200		pF
C_{oes}	Output Capacitance	$V_{CE} = 25V$		295		
C_{res}	Reverse Transfer Capacitance	$f = 1MHz$		20		
Q_g	Total gate Charge	$V_{GE} = 15V$		90		nC
Q_{ge}	Gate - Emitter Charge	$V_{Bus} = 300V$		20		
Q_{gc}	Gate - Collector Charge	$I_C = 30A$		30		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = 15V$ $V_{Bus} = 400V$ $I_C = 30A$ $R_G = 5\Omega$		13		ns
T_r	Rise Time			18		
$T_{d(off)}$	Turn-off Delay Time			55		
T_f	Fall Time			46		
E_{on1}	Turn-on Switching Energy			260		μJ
E_{on2}	Turn-on Switching Energy ❶			335		
E_{off}	Turn-off Switching Energy ❷			250		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = 15V$ $V_{Bus} = 400V$ $I_C = 30A$ $R_G = 5\Omega$		13		ns
T_r	Rise Time			18		
$T_{d(off)}$	Turn-off Delay Time			84		
T_f	Fall Time			80		
E_{on1}	Turn-on Switching Energy			260		μJ
E_{on2}	Turn-on Switching Energy ❶			508		
E_{off}	Turn-off Switching Energy ❷			518		

❶ E_{on2} includes diode reverse recovery

❷ In accordance with JEDEC standard JESD24-1

Temperature sensor NTC

Symbol	Characteristic	Min	Typ	Max	Unit
R_{25}	Resistance @ 25°C		68		$k\Omega$
$B_{25/85}$	$T_{25} = 298.16\text{ K}$		4080		K

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

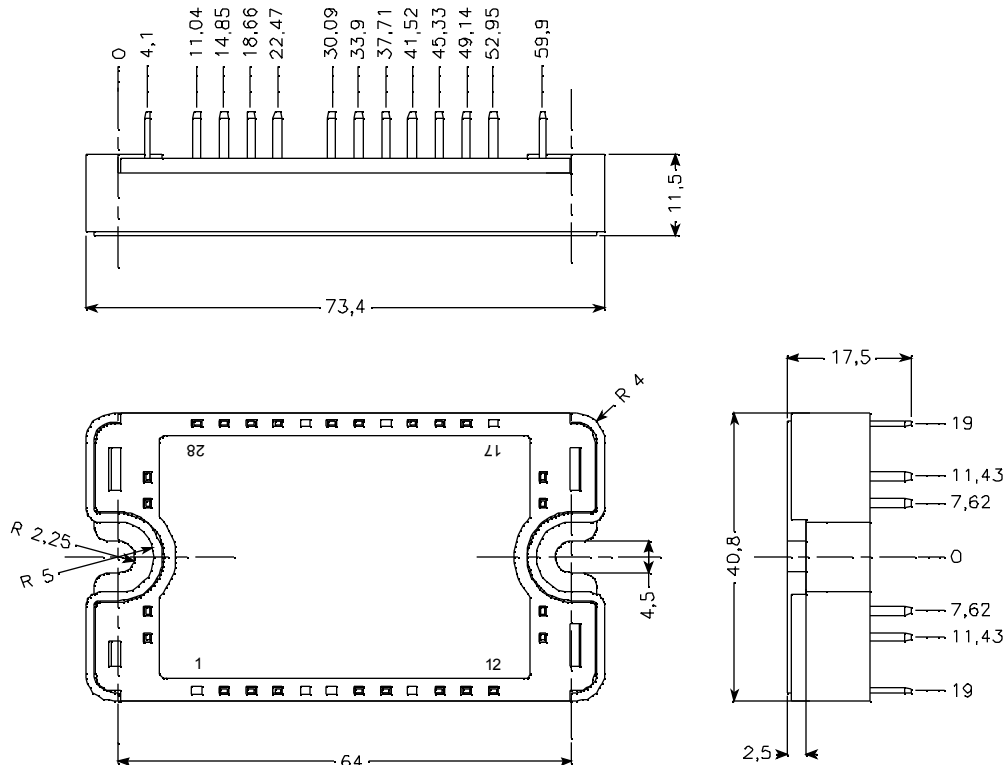
Diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I _{RM}	Maximum Reverse Leakage Current	V _R =600V	T _j = 25°C			250	μA
			T _j = 125°C			500	
I _{F(AV)}	Maximum Average Forward Current	50% duty cycle	T _c = 85°C		30		A
V _F	Diode Forward Voltage	I _F = 30A			2.2	2.7	V
		I _F = 60A			2.7		
		I _F = 30A	T _j = 150°C		1.5		
t _{rr}	Reverse Recovery Time	I _F = 30A V _R = 400V di/dt =200A/μs	T _j = 25°C		74		ns
			T _j = 100°C		74		
Q _{rr}	Reverse Recovery Charge		T _j = 25°C		123		nC
			T _j = 100°C		288		

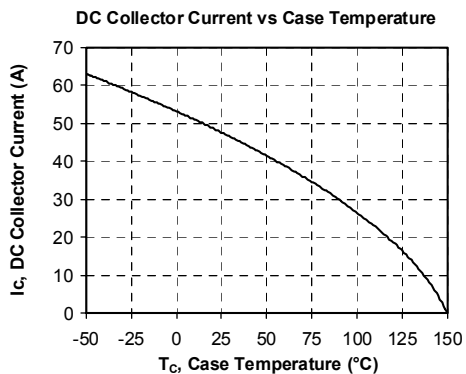
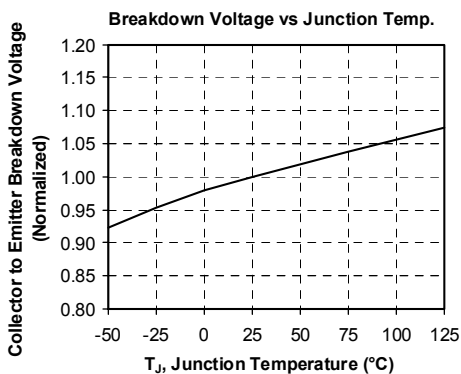
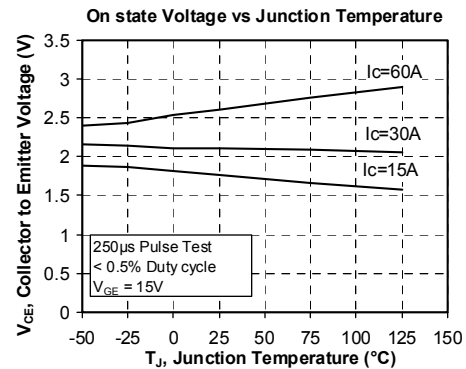
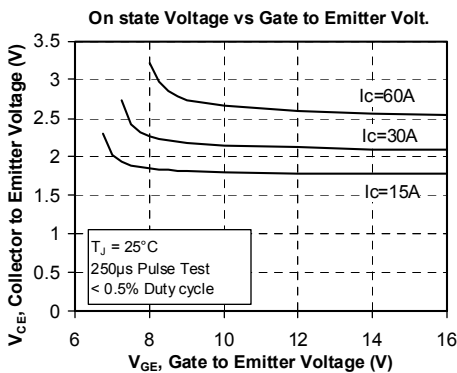
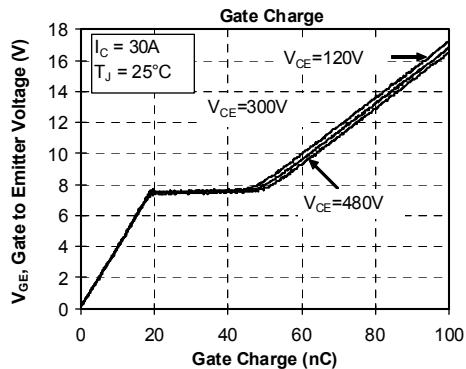
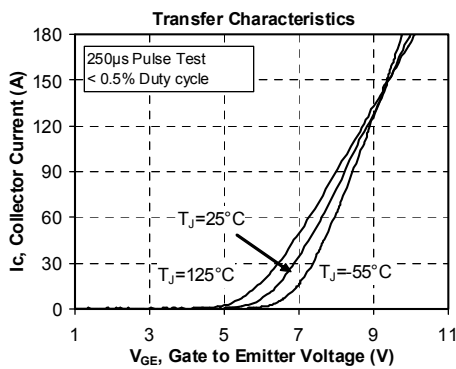
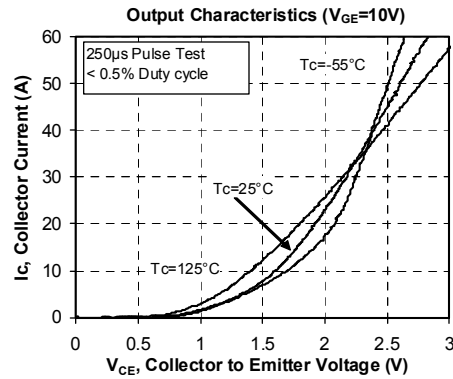
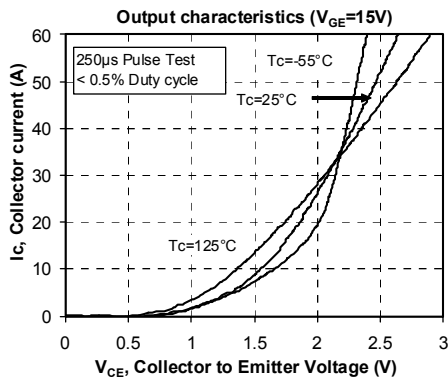
Thermal and package characteristics

Symbol	Characteristic			Min	Typ	Max	Unit
R _{thJC}	Junction to Case			IGBT		0.8	°C/W
				Diode		1.2	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			2500			V
T _J	Operating junction temperature range			-40		150	°C
T _{STG}	Storage Temperature Range			-40		125	
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4			4.7	N.m
Wt	Package Weight					110	g

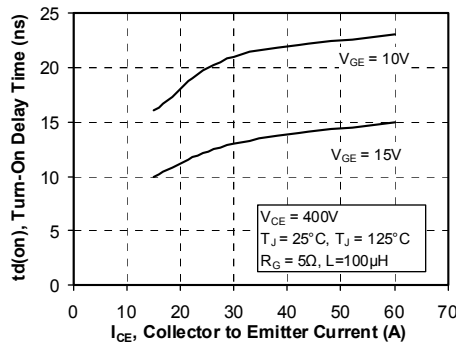
Package outline



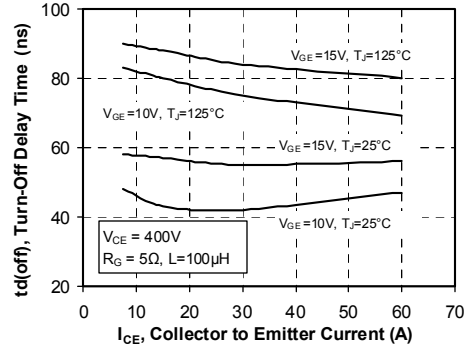
Typical Performance Curve



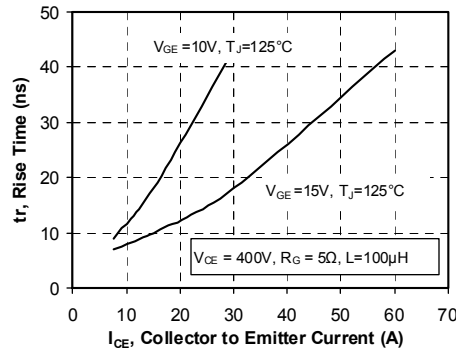
Turn-On Delay Time vs Collector Current



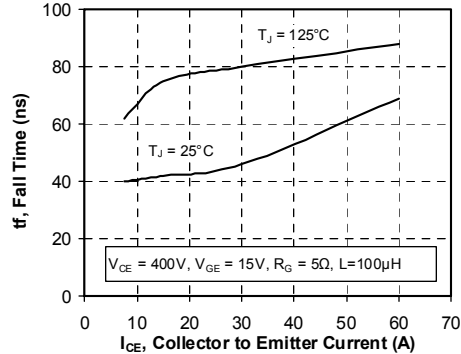
Turn-Off Delay Time vs Collector Current



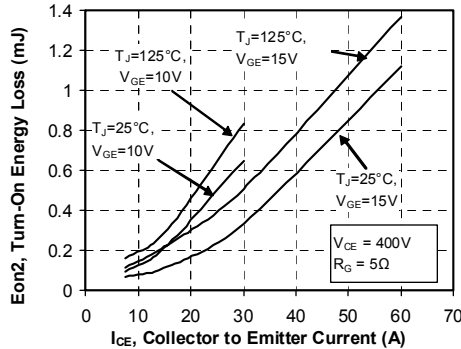
Current Rise Time vs Collector Current



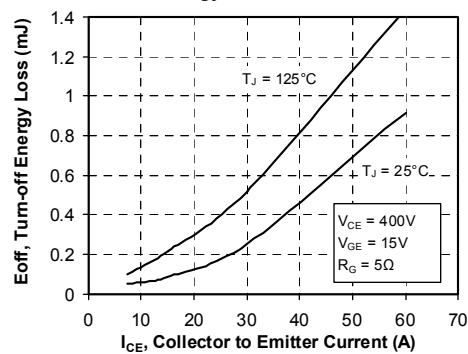
Current Fall Time vs Collector Current



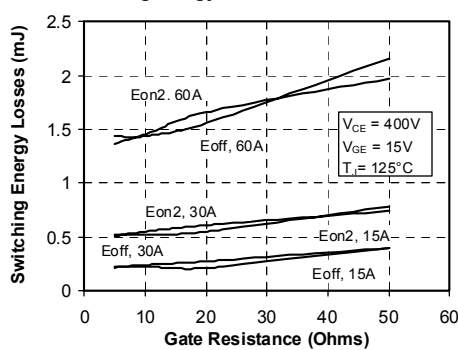
Turn-On Energy Loss vs Collector Current



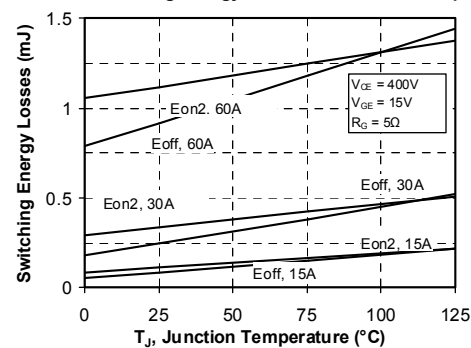
Turn-Off Energy Loss vs Collector Current

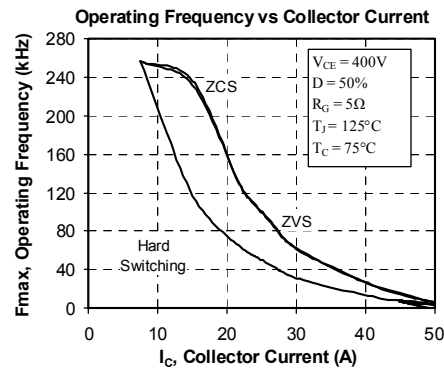
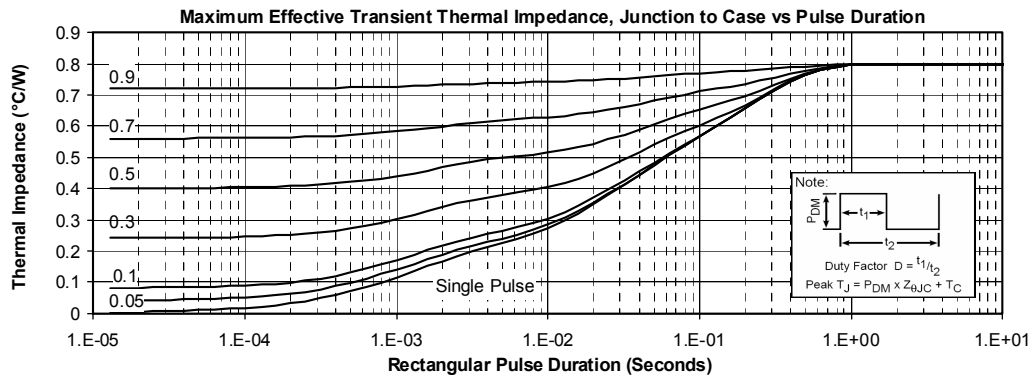
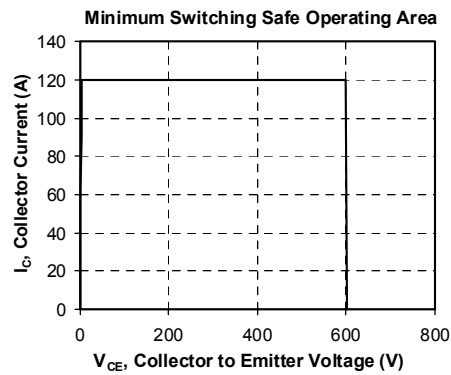
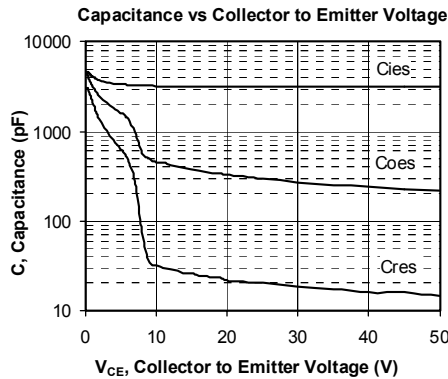


Switching Energy Losses vs Gate Resistance



Switching Energy Losses vs Junction Temp.





APT reserves the right to change, without notice, the specifications and information contained herein

APT's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.